Po-Chun Chang

List of Publications by Year
in descending order

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12 papers	149 citations	1307594 7 h-index	1588992 8 g-index
12 all docs	12 docs citations	12 times ranked	224 citing authors

#	Article	IF	Citations
1	High-Performance Normally-OFF GaN MIS-HEMTs Using Hybrid Ferroelectric Charge Trap Gate Stack (FEG-HEMT) for Power Device Applications. IEEE Electron Device Letters, 2018, 39, 991-994.	3.9	35
2	Normally-OFF GaN MIS-HEMT With F^{âˆ’} Doped Gate Insulator Using Standard Ion Implantation. IEEE Journal of the Electron Devices Society, 2018, 6, 893-899.	2.1	29
3	Normally-Off Tri-Gate GaN MIS-HEMTs with 0.76 mÎ©Â·cm² Specific On-Resistance for Power Device Applications. IEEE Transactions on Electron Devices, 2019, 66, 3441-3446.	3.0	26
4	High-Performance GaN MOSHEMTs Fabricated With ALD Al₂O₃Dielectric and NBE Gate Recess Technology for High Frequency Power Applications. IEEE Electron Device Letters, 2017, 38, 771-774.	3.9	21
5	AlGaN/GaN HEMTs With Damage-Free Neutral Beam Etched Gate Recess for High-Performance Millimeter-Wave Applications. IEEE Electron Device Letters, 2016, 37, 1395-1398.	3.9	16
6	InGaAs Junctionless FinFETs with Self-Aligned Ni-InGaAs S/D. IEEE Journal of the Electron Devices Society, 2018, , 1-1.	2.1	10
7	Electrical Analysis and PBTI Reliability of In_{0.53}Ga_{0.47}As MOSFETs With AlN Passivation Layer and NH₃Postremote Plasma Treatment. IEEE Transactions on Electron Devices, 2016, 63, 3466-3472.	3.0	8
8	InGaAs QW-MOSFET Performance Improvement Using a PEALD-AlN Passivation Layer and an <italic>In-Situ</italic> NH₃Post Remote-Plasma Treatment. IEEE Electron Device Letters, 2017, 38, 310-313.	3.9	4
9	In<inf>x</inf> Ga<inf>1−x</inf> As materials for post CMOS application: Materials and device aspects. , 2014, , .		0
10	HfO2/AlN/In0.53Ga0.47As MOS devices electrical properties and reliability studies. , 2016, , .		0
11	Study on the electrical characteristics of in situ PEALD-passivated HfO2/In0.53Ga0.47As MOSCAP and MOSFET structures. , 2016, , .		0
12	Corrections to â€œAlGaN/GaN HEMTs With Damage-Free Neutral Beam Etched Gate Recess for High-Performance Millimeter-Wave Applicationsâ€•[Nov 16 1395-1398]. IEEE Electron Device Letters, 2017, 38, 149-149.	3.9	0